2N3906

Preferred Device

General Purpose Transistors

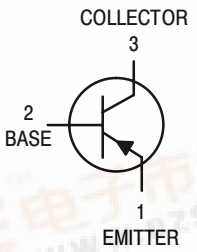
PNP Silicon

ON Semiconductor®

http://onsemi.com

Features

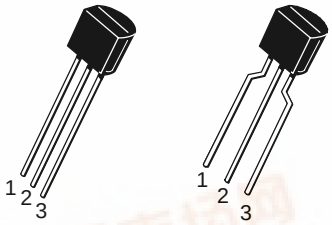
- Pb−Free Packages are Available*



MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector − Emitter Voltage	V_{CEO}	40	Vdc
Collector − Base Voltage	V_{CBO}	40	Vdc
Emitter − Base Voltage	V_{EBO}	5.0	Vdc
Collector Current − Continuous	I_C	200	mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	625 5.0	mW mW/°C
Total Power Dissipation @ T_A = 60°C	P_D	250	mW
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.5 12	W mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

TO−92
CASE 29
STYLE 1



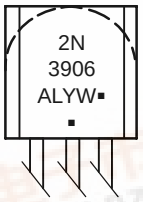
THERMAL CHARACTERISTICS (Note 1)

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction−to−Case	$R_{\theta JC}$	83.3	°C/W

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Indicates Data in addition to JEDEC Requirements.

MARKING DIAGRAM



A = Assembly Location
L = Wafer Lot
Y = Year
W = Work Week
▪ = Pb−Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 3 of this data sheet.

Preferred devices are recommended choices for future use and best overall value.

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

Publication Order Number:

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

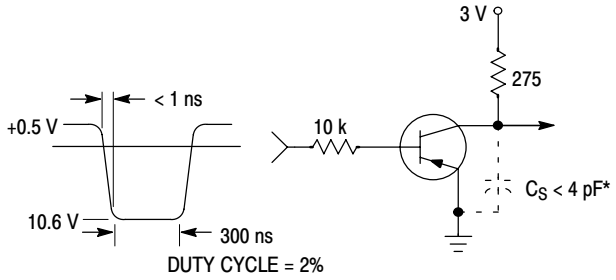
Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector−Emitter Breakdown Voltage (Note 2)	(I_C = 1.0 mAdc, I_B = 0)	$V_{(BR)CEO}$	40	−	Vdc
Collector−Base Breakdown Voltage	(I_C = 10 μAdc, I_E = 0)	$V_{(BR)CBO}$	40	−	Vdc
Emitter−Base Breakdown Voltage	(I_E = 10 μAdc, I_C = 0)	$V_{(BR)EBO}$	5.0	−	Vdc
Base Cutoff Current	(V_{CE} = 30 Vdc, V_{EB} = 3.0 Vdc)	I_{BL}	−	50	nAdc
Collector Cutoff Current	(V_{CE} = 30 Vdc, V_{EB} = 3.0 Vdc)	I_{CEX}	−	50	nAdc
ON CHARACTERISTICS (Note 2)					
DC Current Gain	(I_C = 0.1 mAdc, V_{CE} = 1.0 Vdc) (I_C = 1.0 mAdc, V_{CE} = 1.0 Vdc) (I_C = 10 mAdc, V_{CE} = 1.0 Vdc) (I_C = 50 mAdc, V_{CE} = 1.0 Vdc) (I_C = 100 mAdc, V_{CE} = 1.0 Vdc)	h_{FE}	60 80 100 60 30	− − 300 − −	−
Collector−Emitter Saturation Voltage	(I_C = 10 mAdc, I_B = 1.0 mAdc) (I_C = 50 mAdc, I_B = 5.0 mAdc	$V_{CE(sat)}$	− −	0.25 0.4	Vdc
Base−Emitter Saturation Voltage	(I_C = 10 mAdc, I_B = 1.0 mAdc) (I_C = 50 mAdc, I_B = 5.0 mAdc)	$V_{BE(sat)}$	0.65 −	0.85 0.95	Vdc
SMALL−SIGNAL CHARACTERISTICS					
Current−Gain − Bandwidth Product	(I_C = 10 mAdc, V_{CE} = 20 Vdc, f = 100 MHz)	f_T	250	−	MHz
Output Capacitance	(V_{CB} = 5.0 Vdc, I_E = 0, f = 1.0 MHz)	C_{obo}	−	4.5	pF
Input Capacitance	(V_{EB} = 0.5 Vdc, I_C = 0, f = 1.0 MHz)	C_{ibo}	−	10	pF
Input Impedance	(I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	h_{ie}	2.0	12	kΩ
Voltage Feedback Ratio	(I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	h_{re}	0.1	10	X 10^{-4}
Small−Signal Current Gain	(I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	h_{fe}	100	400	−
Output Admittance	(I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	h_{oe}	3.0	60	μmhos
Noise Figure	(I_C = 100 μAdc, V_{CE} = 5.0 Vdc, R_S = 1.0 kΩ, f = 1.0 kHz)	NF	−	4.0	dB
SWITCHING CHARACTERISTICS					
Delay Time	(V_{CC} = 3.0 Vdc, V_{BE} = 0.5 Vdc, I_C = 10 mAdc, I_{B1} = 1.0 mAdc)	t_d	−	35	ns
Rise Time		t_r	−	35	ns
Storage Time	(V_{CC} = 3.0 Vdc, I_C = 10 mAdc, I_{B1} = I_{B2} = 1.0 mAdc)	t_s	−	225	ns
Fall Time	(V_{CC} = 3.0 Vdc, I_C = 10 mAdc, I_{B1} = I_{B2} = 1.0 mAdc)	t_f	−	75	ns

2. Pulse Test: Pulse Width ≤ 300 μs; Duty Cycle ≤ 2%.

ORDERING INFORMATION

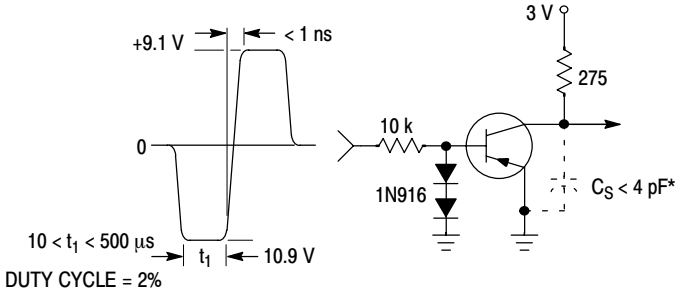
Device	Package	Shipping†
2N3906	TO−92	5000 Units / Bulk
2N3906G	TO−92 (Pb−Free)	5000 Units / Bulk
2N3906RL1	TO−92	5000 Units / Bulk
2N3906RL1G	TO−92 (Pb−Free)	5000 Units / Bulk
2N3906RLRA	TO−92	2000 / Tape & Reel
2N3906RLRAG	TO−92 (Pb−Free)	2000 / Tape & Reel
2N3906RLRM	TO−92	2000 / Ammo Pack
2N3906RLRMG	TO−92 (Pb−Free)	2000 / Ammo Pack
2N3906RLRP	TO−92	2000 / Tape & Reel
2N3906RLRPG	TO−92 (Pb−Free)	2000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



* Total shunt capacitance of test jig and connectors

Figure 1. Delay and Rise Time Equivalent Test Circuit



* Total shunt capacitance of test jig and connectors

Figure 2. Storage and Fall Time Equivalent Test Circuit

TYPICAL TRANSIENT CHARACTERISTICS

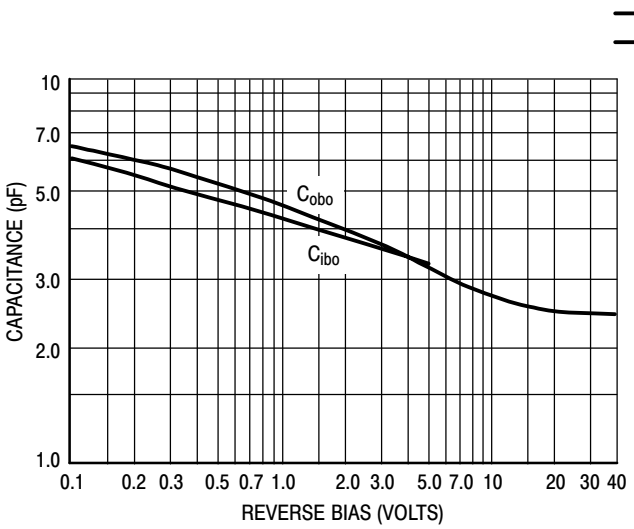


Figure 3. Capacitance

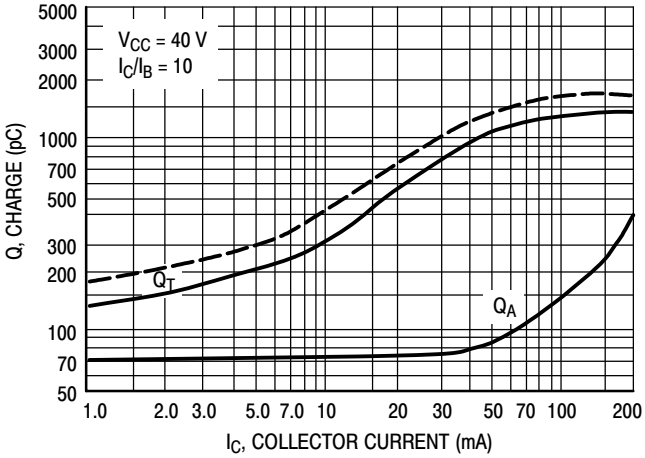


Figure 4. Charge Data

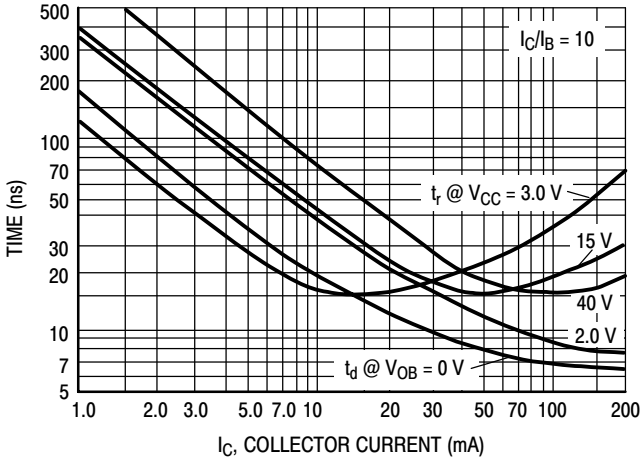


Figure 5. Turn−On Time

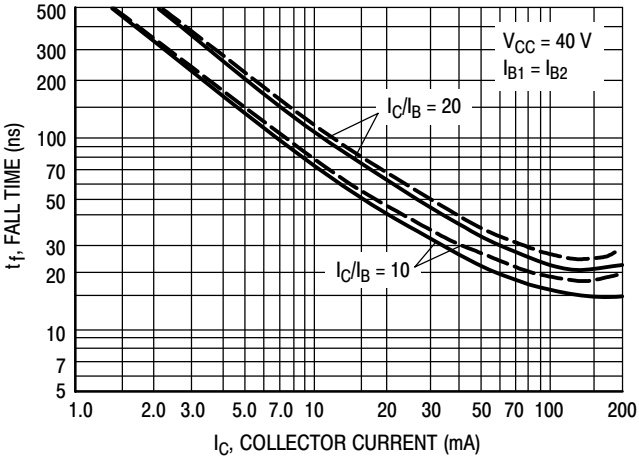


Figure 6. Fall Time

TYPICAL AUDIO SMALL−SIGNAL CHARACTERISTICS
NOISE FIGURE VARIATIONS

(V_{CE} = −5.0 Vdc, T_A = 25°C, Bandwidth = 1.0 Hz)

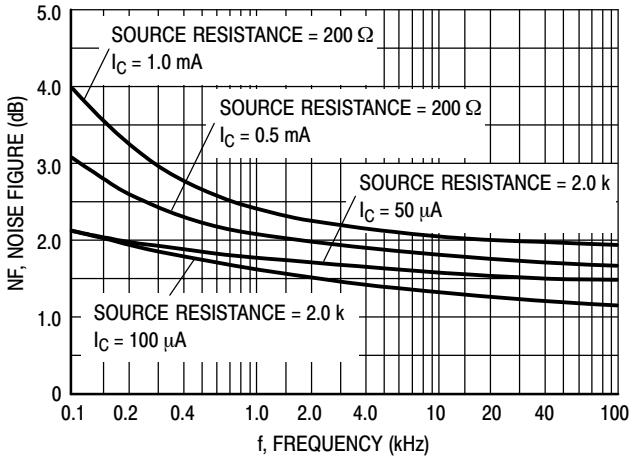


Figure 7.

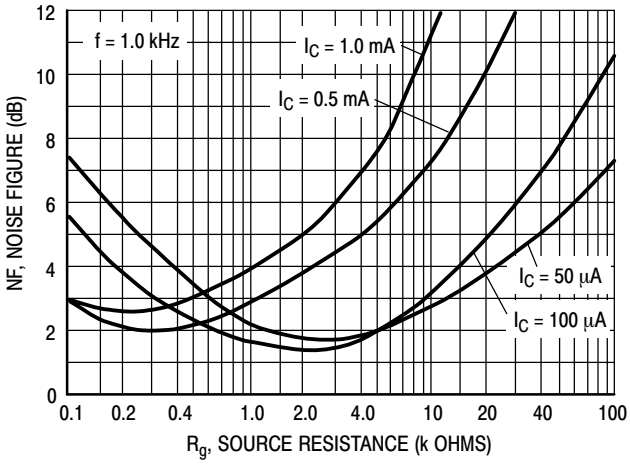


Figure 8.

h PARAMETERS

(V_{CE} = −10 Vdc, f = 1.0 kHz, T_A = 25°C)

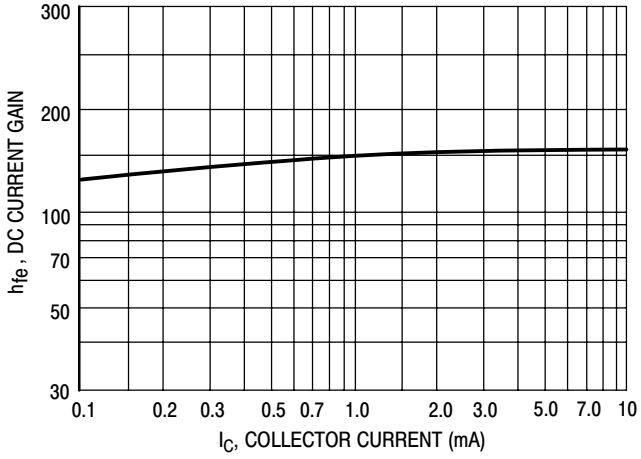


Figure 9. Current Gain

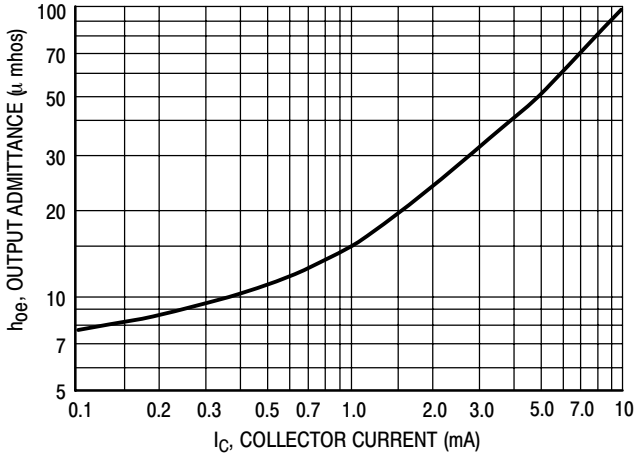


Figure 10. Output Admittance

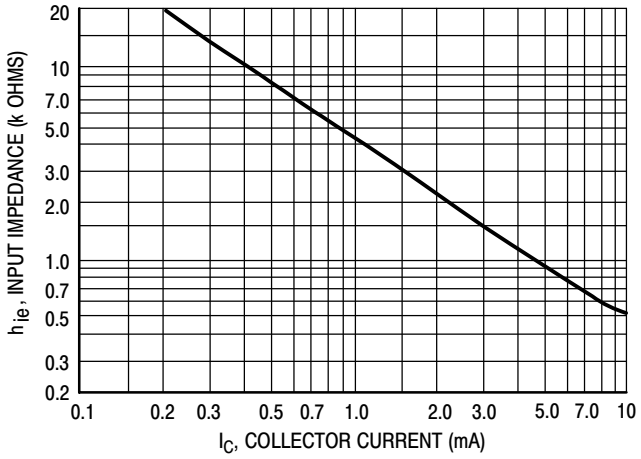


Figure 11. Input Impedance

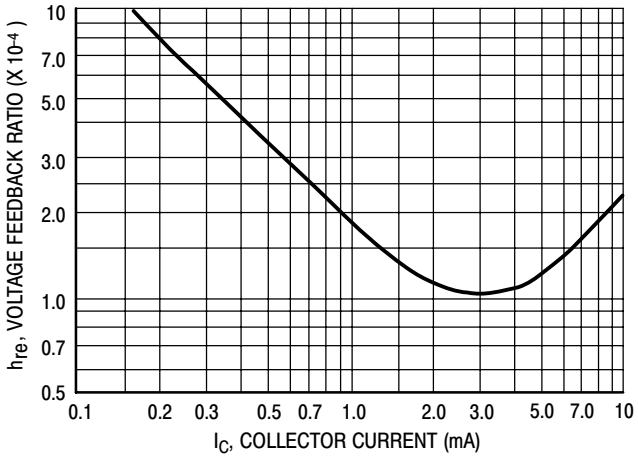


Figure 12. Voltage Feedback Ratio

TYPICAL STATIC CHARACTERISTICS

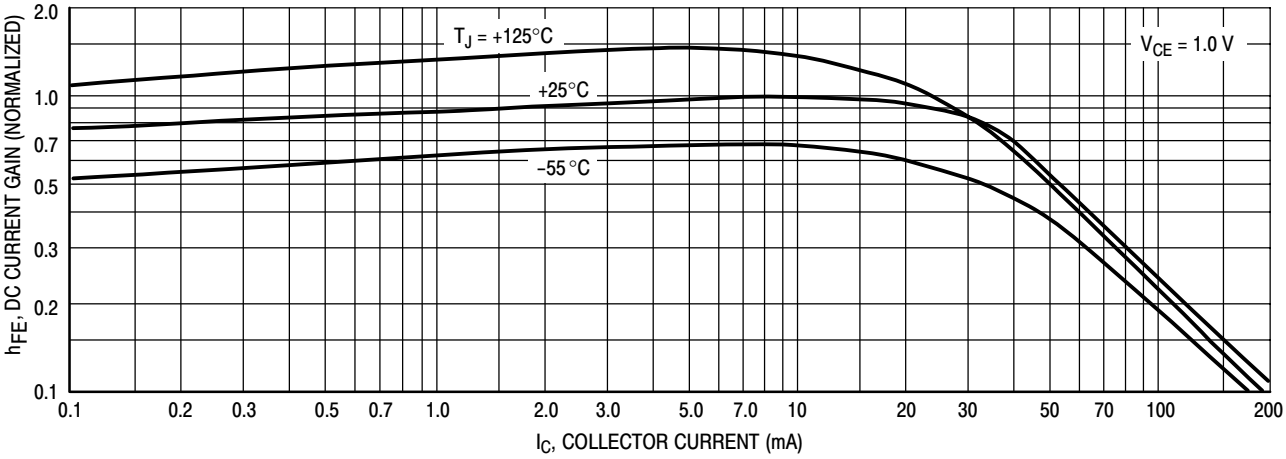


Figure 13. DC Current Gain

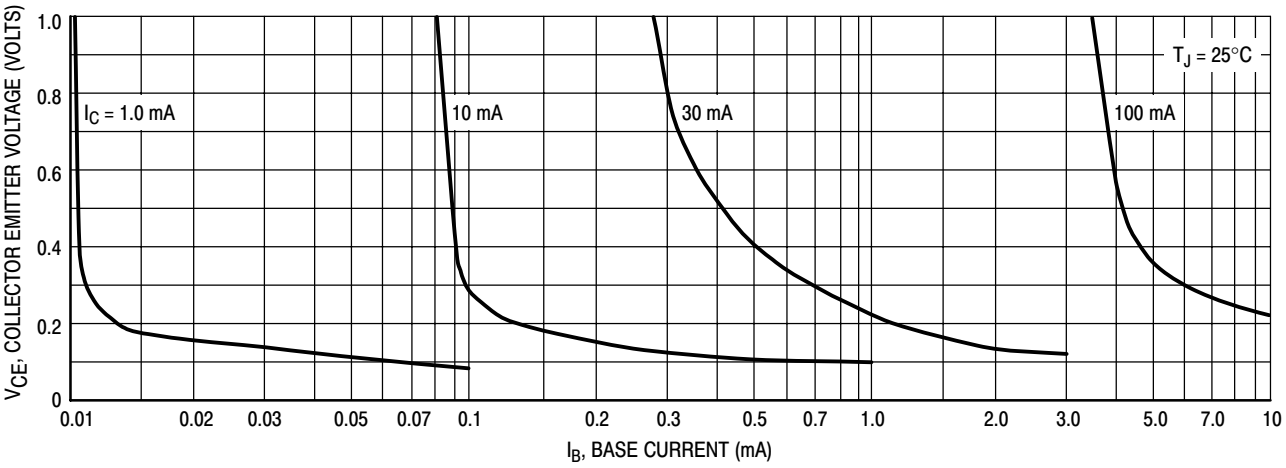


Figure 14. Collector Saturation Region

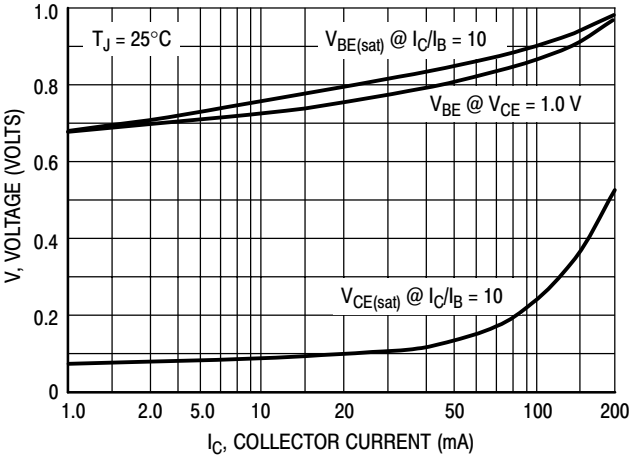


Figure 15. “ON” Voltages

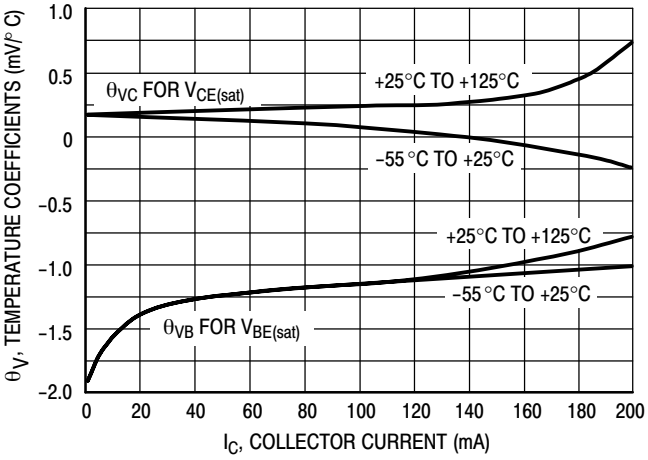
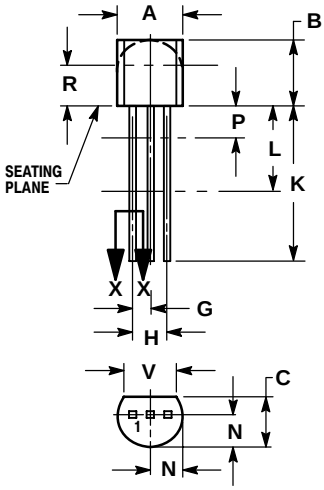


Figure 16. Temperature Coefficients

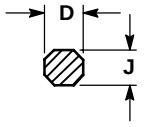
2N3906

PACKAGE DIMENSIONS

TO−92 (TO−226)
CASE 29−11
ISSUE AM



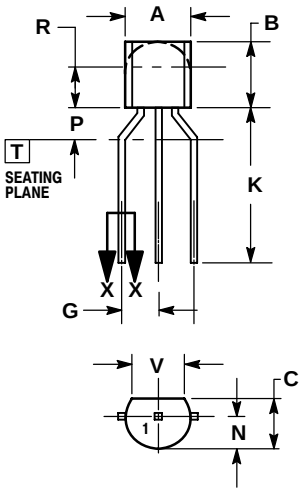
STRAIGHT LEAD
BULK PACK



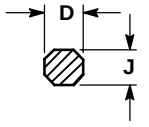
SECTION X−X

NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.175	0.205	4.45	5.20
B	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500	---	12.70	---
L	0.250	---	6.35	---
N	0.080	0.105	2.04	2.66
P	---	0.100	---	2.54
R	0.115	---	2.93	---
V	0.135	---	3.43	---



BENT LEAD
TAPE & REEL
AMMO PACK



SECTION X−X

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	MILLIMETERS	
DIM	MIN	MAX
A	4.45	5.20
B	4.32	5.33
C	3.18	4.19
D	0.40	0.54
G	2.40	2.80
J	0.39	0.50
K	12.70	---
N	2.04	2.66
P	1.50	4.00
R	2.93	---
V	3.43	---

STYLE 1:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA
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